

OA180

Gold Bonded Germanium Diode

FEATURES

Low forward voltage drop—low power consumption
Thirty years of proven reliability—one million hours mean time between failures (MTBF)
Very low noise level
Metallurgically bonded

ABSOLUTE MAXIMUM RATINGS (at 25 °C, unless otherwise specified)

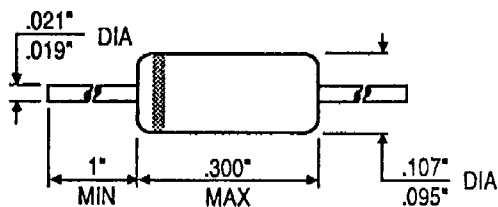
Peak Inverse Voltage	20 Volts
Peak Forward Current	500 mA
Operating Temperature	- 65 °C to 85 °C
Average Power Dissipation	80 mW

ELECTRICAL CHARACTERISTICS

	Symbol	Conditions	Min	Max	Unit	T °C
Peak Inverse Voltage	PIV	1 mA	20		V	25 °C
Reverse Current	I _r	10 V		20	μA	25 °C
Forward Voltage	V _f	100 mA		0.75	V	25 °C
Reverse Recovery	T _{rr}	See note		70		

NOTE: I_f = 10, V_r = 1, Recover to 10 mA.

MECHANICAL



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